

2SK2373

Silicon N-Channel MOS FET

HITACHI

ADE-208-268 (Z)
1st. Edition
Mar. 2001

Application

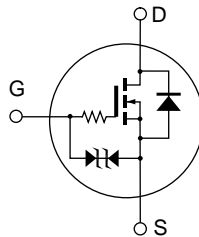
Low frequency power switching

Features

- Low on-resistance
- Small package
- Low drive current
- 4 V gate drive device can be driven from 5 V source.
- Suitable for low signal load switch

Outline

MPAK



1. Source
2. Gate
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

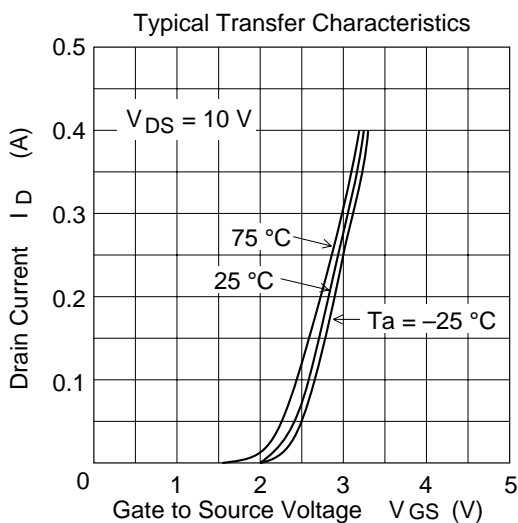
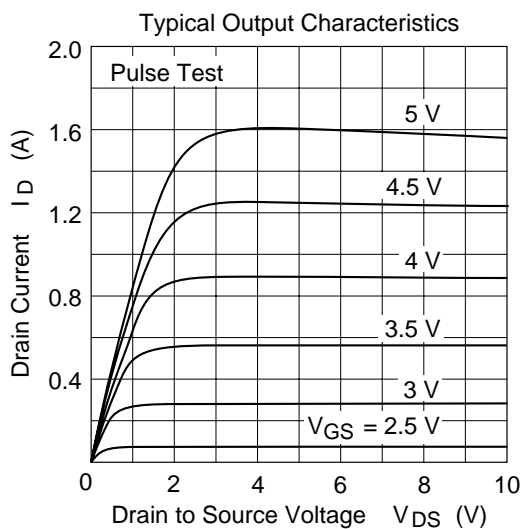
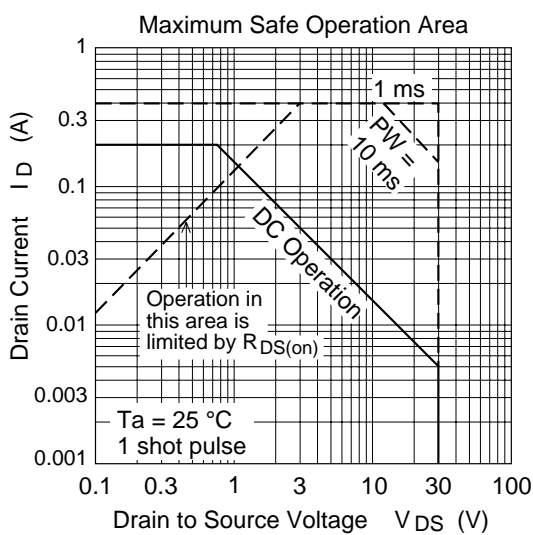
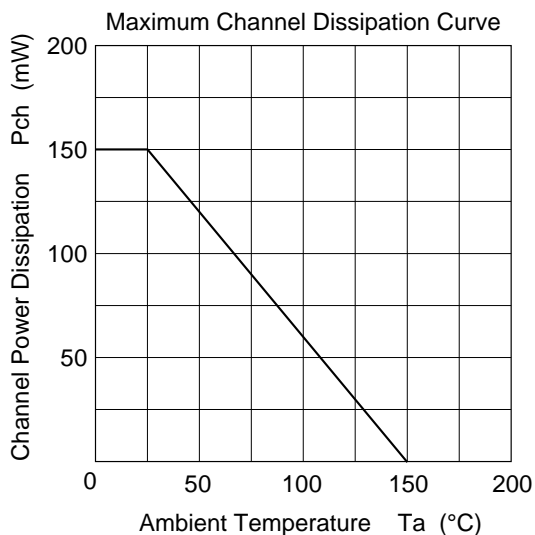
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	0.2	A
Drain peak current	$I_{D(pulse)}^{*1}$	0.4	A
Body to drain diode reverse drain current	I_{DR}	0.2	A
Channel dissipation	Pch^{*2}	150	mW
Channel temperature	Tch	150	°C
Storage temperature	$Tstg$	-55 to +150	°C

- Notes 1. $PW \leq 100 \mu s$, duty cycle $\leq 10 \%$
 2. Marking is "ZE-".

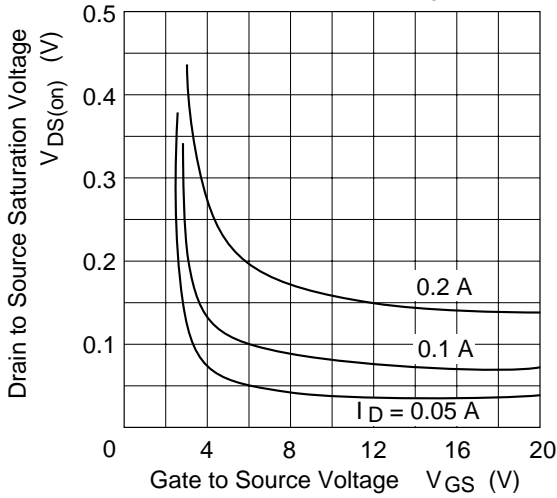
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 100 \mu A$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±2	μA	$V_{GS} = \pm 16 V$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30 V$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 10 \mu A$, $V_{DS} = 5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.4	2.5	Ω	$I_D = 20 mA$ $V_{GS} = 4 V^{*1}$
		—	1.0	1.4	Ω	$I_D = 10 mA$ $V_{GS} = 10 V^{*1}$
Input capacitance	C_{iss}	—	17.8	—	pF	$V_{DS} = 10 V$
Output capacitance	C_{oss}	—	25.4	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	3.7	—	pF	$f = 1 MHz$
Turn-on delay time	$t_{d(on)}$	—	50	—	ns	$I_D = 0.1 A$
Rise time	t_r	—	125	—	ns	$V_{GS} = 10 V$
Turn-off delay time	$t_{d(off)}$	—	660	—	ns	$R_L = 100 \Omega$
Fall time	t_f	—	400	—	ns	$PW = 2 \mu s$

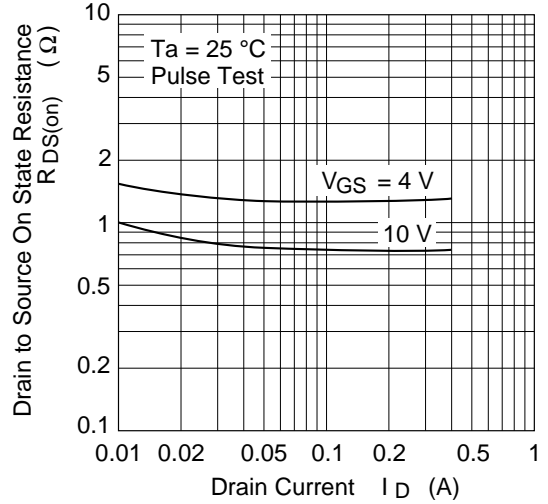
Note 1. Pulse Test



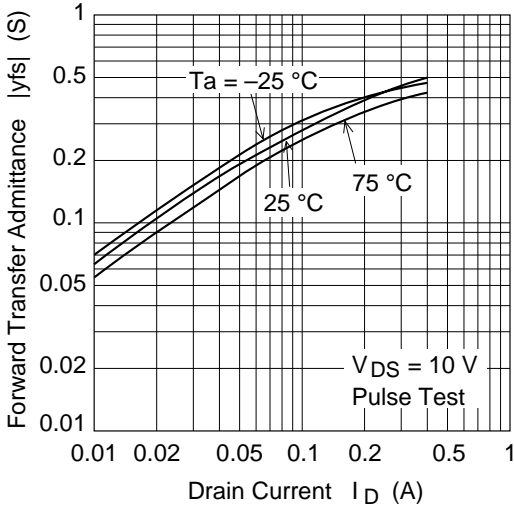
Drain to Source Saturation Voltage vs. Gate to Source Voltage



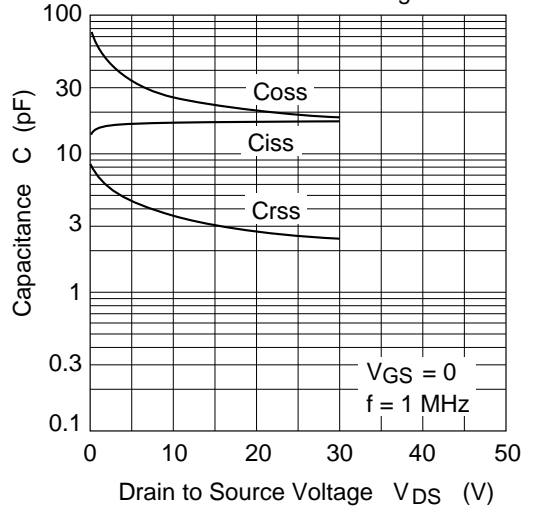
Static Drain to Source on State Resistance vs. Drain Current

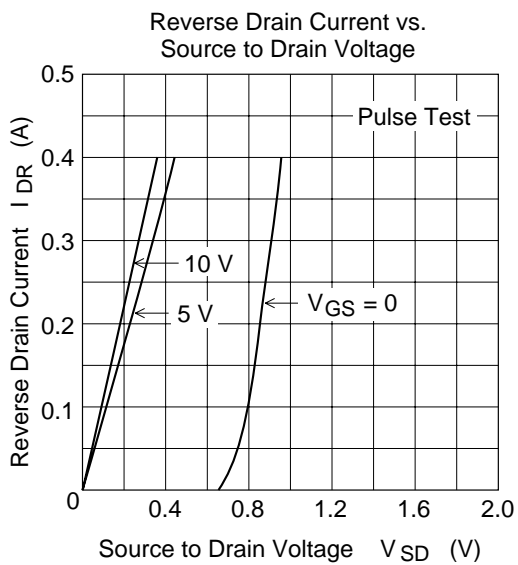


Forward Transfer Admittance vs. Drain Current



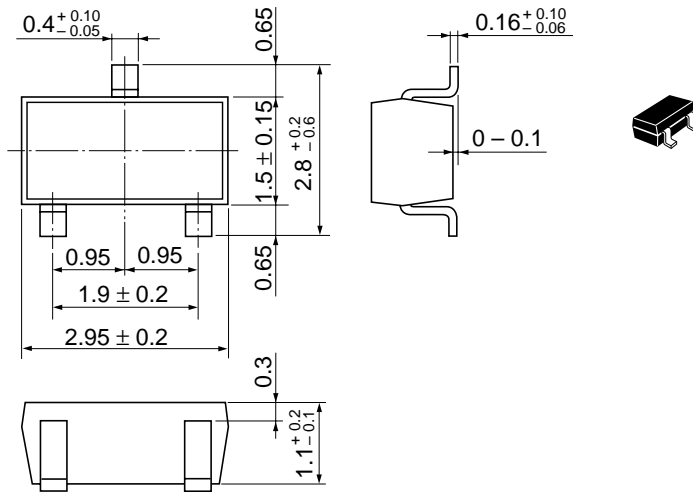
Typical Capacitance vs. Drain to Source Voltage





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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